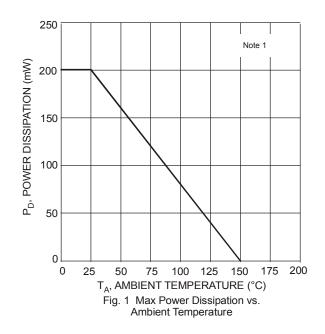
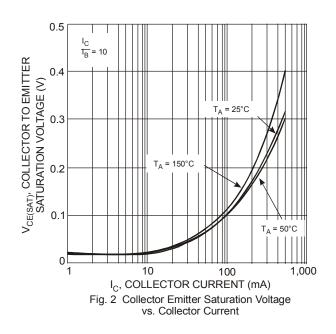


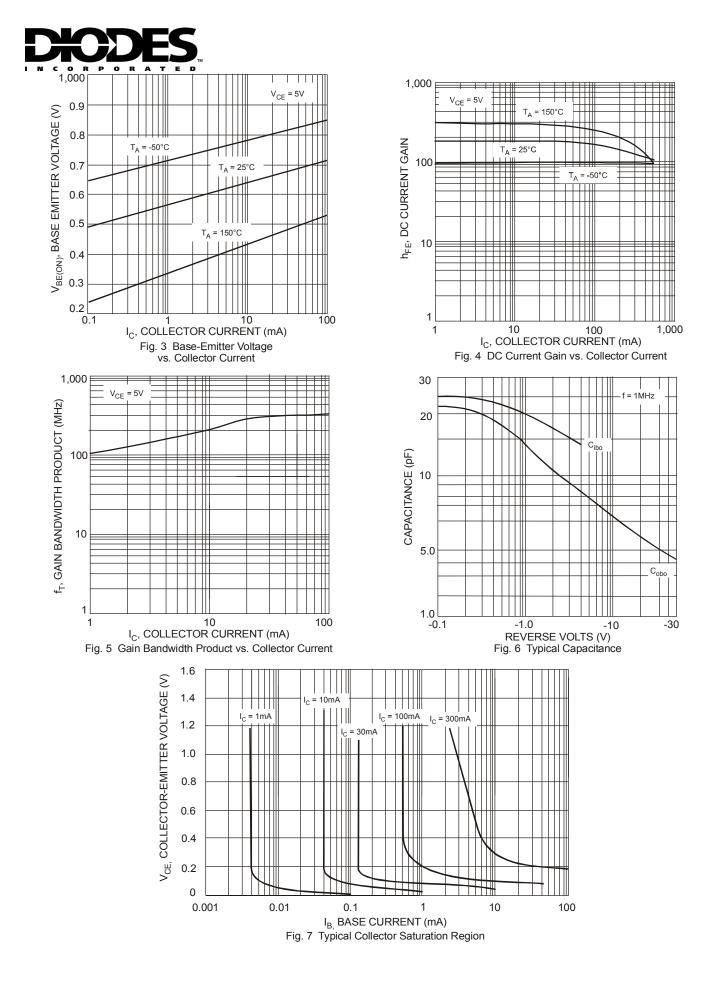
Electrical Characteristics @T <sub>A</sub> = 25°C unless otherwise specified									
Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 6)									
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40	_	V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$				
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-40	_	V	$I_{\rm C}$ = -1.0mA, $I_{\rm B}$ = 0				
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	_	V	$I_{\rm E} = -100 \mu A, I_{\rm C} = 0$				
Collector Cutoff Current	I <sub>CEX</sub>	_	-100	nA	$V_{CE} = -35V, V_{EB(OFF)} = -0.4V$				
Base Cutoff Current	I <sub>BL</sub>	_	-100	nA	$V_{CE}$ = -35V, $V_{EB(OFF)}$ = -0.4V				
ON CHARACTERISTICS (Note 6)			-						
DC Current Gain	h <sub>FE</sub>	30 60 100 100 20	  300 	_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} &= -1.0 V \\ I_{C} &= -1.0 m A, \ V_{CE} &= -1.0 V \\ I_{C} &= -10 m A, \ V_{CE} &= -1.0 V \\ I_{C} &= -150 m A, \ V_{CE} &= -2.0 V \\ I_{C} &= -500 m A, \ V_{CE} &= -2.0 V \end{split}$				
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		-0.40 -0.75	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA				
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.75	-0.95 -1.30	v	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA				
SMALL SIGNAL CHARACTERISTICS			-						
Output Capacitance	C <sub>cb</sub>	_	8.5	pF	$V_{CB}$ = -10V, f = 1.0MHz, I <sub>E</sub> = 0				
Input Capacitance	Ceb	_	30	pF	$V_{EB}$ = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0				
Input Impedance	h <sub>ie</sub>	1.5	15	kΩ					
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10⁻⁴	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA,				
Small Signal Current Gain	h <sub>fe</sub>	60	500		f = 1.0kHz				
Output Admittance	h <sub>oe</sub>	1.0	100	μS					
Current Gain-Bandwidth Product	f <sub>T</sub>	200	—	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -20mA, f = 100MHz				
SWITCHING CHARACTERISTICS									
Delay Time	t <sub>d</sub>	_	15	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,				
Rise Time	t <sub>r</sub>	_	20	ns	$V_{BE(off)} = -2.0V, I_{B1} = -15mA$				
Storage Time	ts	_	225	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,				
Fall Time	t <sub>f</sub>	_	30	ns	$I_{B1} = I_{B2} = -15 \text{mA}$				

Notes: 6. Short duration pulse test used to minimize self-heating effect.





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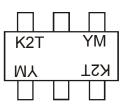


## Ordering Information (Note 7)

Device	Packaging	Shipping				
MMDT4403-7-F	SOT-363	3000/Tape & Reel				

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



K2T = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Feb	<b>)</b>	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	lov	Dec
Code	4	2		2	4	5	6		7	0	0	0		Ν	Р

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